

Introduction

Topological Insulator:

Low Energy Action:

$$S = S_{Maxwell} + S_{Axion}$$

$$S_{Axion} = \frac{\theta}{2\pi} \frac{e^2}{2\pi\hbar c} \int d^3x dt \mathbf{E} \cdot \mathbf{B}$$

$$= \hbar\theta N$$

$\theta = \pi$: Topological Magnetoelectric Coupling
Orbital Effect (Band Effect).

Axion Insulator:

Axion Electrodynamics:

$$-\frac{1}{c^2} \frac{\partial \mathbf{E}}{\partial t} + \nabla \times \mathbf{B} = \frac{\alpha}{\pi c} (\dot{\theta} \mathbf{B} + \nabla \theta \times \mathbf{E})$$

$$\nabla \cdot \mathbf{E} = -\frac{\alpha C}{\pi} \nabla \theta \cdot \mathbf{B}$$

TME Current:

$$\mathbf{j} = \frac{e^2}{2\pi h} [\nabla \theta \times \mathbf{E} + \partial_t \theta \mathbf{B}]$$

For Axion insulator thin film, the θ is not quantized and depends on thickness and surface gap.

$$1 - \frac{\theta(d)}{\pi} = \frac{\beta(\Delta_s)}{d} + o\left(\frac{1}{d^2}\right)$$

$$\eta \equiv (d/\pi)(\partial\theta/\partial\Delta_s)$$

Dynamics on surface gap would give θ time dependence.

$$\partial_t \theta = \frac{\partial \theta}{\partial \Delta_s} \frac{\partial \Delta_s}{\partial t}$$

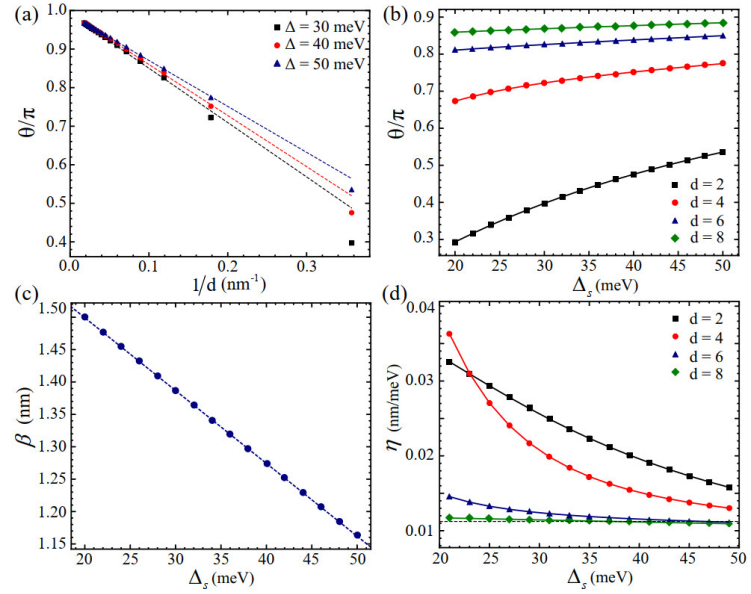
Surface magnetic resonance induced surface gap dynamics.

$$\mathcal{J}_D = \mathcal{J}_D^x \hat{\mathbf{x}} = \frac{e^2}{2h} \eta g_M \partial_t \delta M_z (B_1^x + B_2^x \cos(\omega t)) \hat{\mathbf{x}}$$

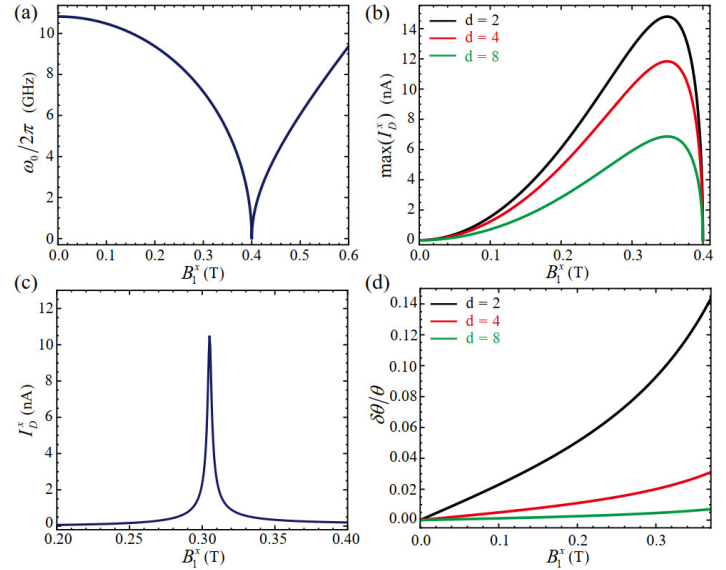
Reference

- [1] X.-L. Qi and S.-C. Zhang, Rev. Mod. Phys. **83**, 1057(2011)
 [2] X.-L. Qi, T. L. Hughes, and S.-C. Zhang, Phys. Rev. B **78**, 195424 (2008)
 [3] Liu Z, Xiao J, Wang J. Dynamical magnetoelectric coupling in axion insulator thin films. arXiv:2007.09869, 2020.

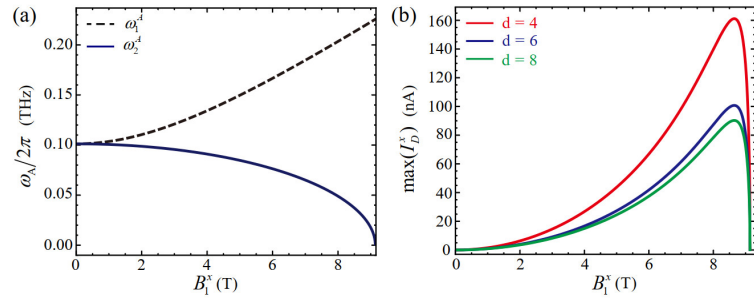
Results



FMR



AFMR



Conclusion

The surface magnetic resonance can induce dynamical magnetoelectric current in Axion insulator thin film.